Silicon NPN Power Transistors 2SC1520

DESCRIPTION

- With TO-202 package
- High voltage
- High transition frequency

APPLICATIONS

- For color TV chroma output and video output applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

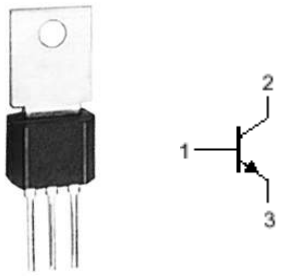

Fig.1 simplified outline (TO-202) and symbol

Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	250	V
V_{CEO}	Collector-emitter voltage	Open base	250	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		0.2	A
P_C	Collector power dissipation	T_a=25℃	1.0	W
		T_C=25℃	10	
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	I_C=50mA ;I_B=5m A			2.0	V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=1mA; I_B=0	250			V
I_{CBO}	Collector cut-off current	V_{CB}=150V ;I_E=0			0.1	μ A
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			0.1	μ A
h_{FE}	DC current gain	I_C=10mA ; V_{CE}=10V	40		200	
C_{OB}	Output capacitance	I_E=0; V_{CB}=50V;f=1MHz			4.5	pF
f_T	Transition frequency	I_C=10mA ; V_{CB}=30V		80		MHz

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PACKAGE OUTLINE

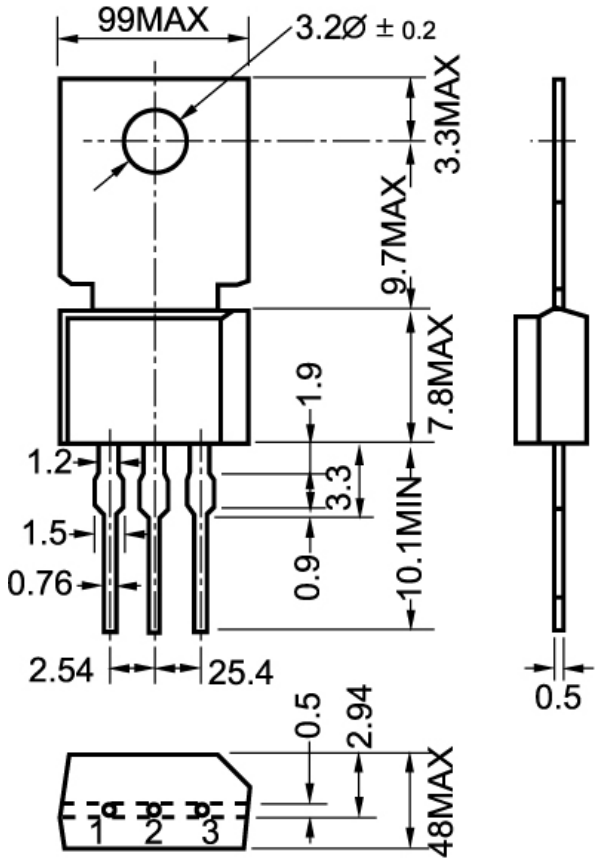

Fig.2 outline dimensions